



DMG1013T

P-CHANNEL ENHANCEMENT MODE MOSFET

Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead Free By Design/RoHS Compliant (Note 2)
- ESD Protected Up To 3kV
- "Green" Device (Note 3)
- Qualified to AEC-Q101 standards for High Reliability

Mechanical Data

Case: SOT-523

 Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0

Moisture Sensitivity: Level 1 per J-STD-020

 Terminals: Finish — Matte Tin annealed over Alloy 42 leadframe. Solderable per MIL-STD-202, Method 208

• Terminal Connections: See Diagram

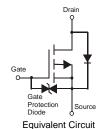
Marking Information: See Page 4

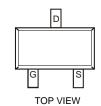
Ordering Information: See Page 4

Weight: 0.002 grams (approximate)

SOT-523







Char	acteristic		Symbol	Value	Units	
Drain-Source Voltage			V_{DSS}	-20	V	
Gate-Source Voltage			V_{GSS}	±6	V	
Drain Current (Note 1)	Steady State	$T_A = 25$ °C $T_A = 85$ °C	I _D	-0.46 -0.33	Α	
Pulsed Drain Current			I _{DM}	-6	A	

Thermal Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 1)	P _D	0.27	W
Thermal Resistance, Junction to Ambient	$R_{ hetaJA}$	461	°C/W
Operating and Storage Temperature Range	T _{J,} T _{STG}	-55 to +150	°C

Notes:

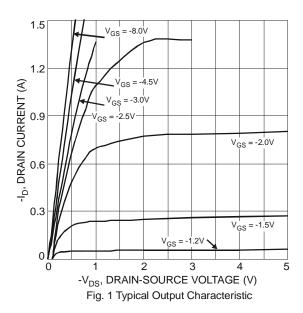
- 1. Device mounted on FR-4 PCB.
- 2. No purposefully added lead.
- 3. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.

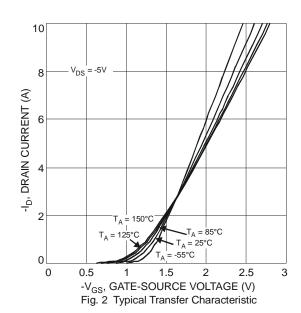


Electrical Characteristics @T_A = 25°C unless otherwise specified

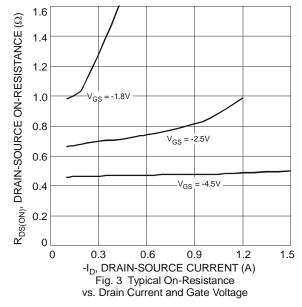
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 4)						
Drain-Source Breakdown Voltage	BV _{DSS}	-20	-	-	V	$V_{GS} = 0V, I_D = -250\mu A$
Zero Gate Voltage Drain Current T _J = 25°C	I _{DSS}	ı	-	-100	nA	$V_{DS} = -20V, V_{GS} = 0V$
Gate-Source Leakage	I_{GSS}	1	-	±2.0	μΑ	$V_{GS} = \pm 4.5 V, V_{DS} = 0 V$
ON CHARACTERISTICS (Note 4)						
Gate Threshold Voltage	V _{GS(th)}	-0.5	-	-1.0	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$
			0.5	0.7		$V_{GS} = -4.5V, I_D = -350mA$
Static Drain-Source On-Resistance	R _{DS (ON)}	-	0.7	0.9	Ω	$V_{GS} = -2.5V, I_D = -300mA$
	, ,		1.0	1.3		$V_{GS} = -1.8V, I_D = -150mA$
Forward Transfer Admittance	Y _{fs}	-	0.9	-	S	$V_{DS} = -10V, I_D = -250mA$
Diode Forward Voltage (Note 4)	V_{SD}		-0.8	-1.2	V	$V_{GS} = 0V, I_{S} = -150mA$
DYNAMIC CHARACTERISTICS	<u>.</u>					
Input Capacitance	C _{iss}	i	59.76	-	pF	101/11/
Output Capacitance	Coss	-	12.07	-	pF	$V_{DS} = -16V, V_{GS} = 0V,$ - f = 1.0MHz
Reverse Transfer Capacitance	C _{rss}	-	6.36	-	pF	1 = 1.000112
Total Gate Charge	Qg	-	622.4	-	рС	V 45V V 40V
Gate-Source Charge	Q _{qs}	-	100.3	-	рС	$V_{GS} = -4.5V, V_{DS} = -10V,$
Gate-Drain Charge	Q _{gd}	-	132.2	-	рС	$I_D = -250 \text{mA}$
Turn-On Delay Time	t _{D(on)}	-	5.1	-	ns	
Turn-On Rise Time	t _r	-	8.1	-	ns	$V_{DD} = -10V, V_{GS} = -4.5V,$
Turn-Off Delay Time	t _{D(off)}	-	28.4	-	ns	$R_L = 47\Omega$, $R_G = 10\Omega$,
Turn-Off Fall Time	t _f	-	20.7	-	ns	$I_D = -200 \text{mA}$

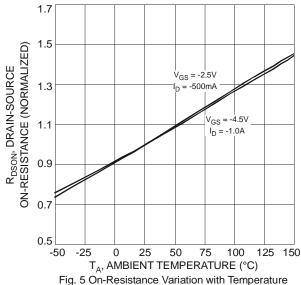
Notes: 4. Short duration pulse test used to minimize self-heating effect.











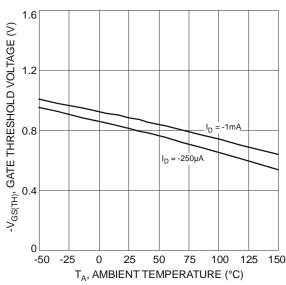
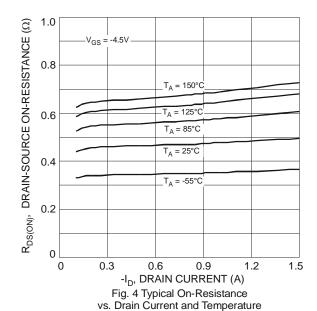


Fig. 7 Gate Threshold Variation vs. Ambient Temperature



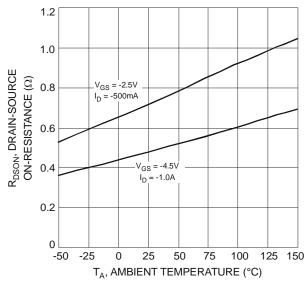
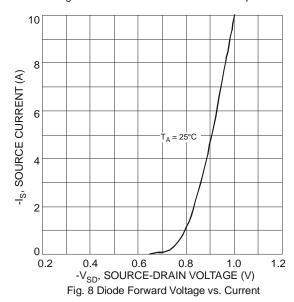
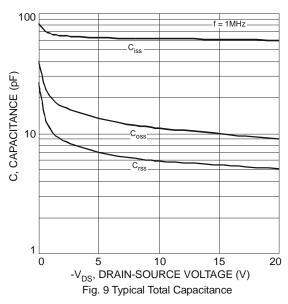


Fig. 6 On-Resistance Variation with Temperature







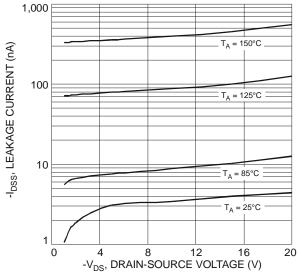
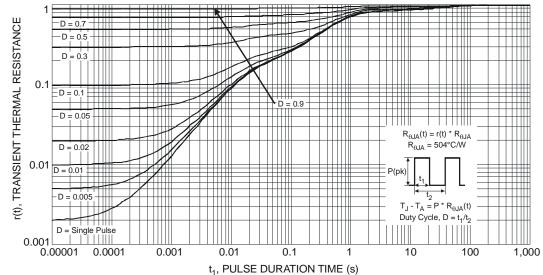


Fig. 10 Typical Leakage Current vs. Drain-Source Voltage



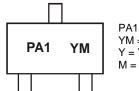
Ordering Information (Note 5)

Part Number	Case	Packaging		
DMG1013T-7	SOT-523	3000/Tape & Reel		

Fig. 11 Transient Thermal Response

Notes: 5. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



PA1 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: W = 2009)

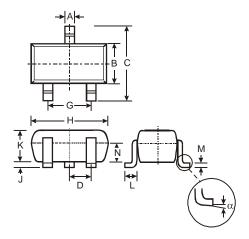
M = Month (ex: 9 = September)

Date Code Key

Year	2009	9	2010		2011	20	12	2013		2014	2	2015
Code	W		X		Υ		Z	Α		В		С
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

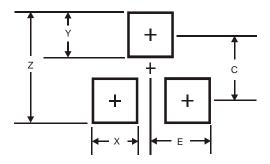


Package Outline Dimensions



SOT-523						
Dim	Min	Max	Тур			
Α	0.15	0.30	0.22			
В	0.75	0.85	0.80			
С	1.45	1.75	1.60			
D		_	0.50			
G	0.90	1.10	1.00			
Н	1.50	1.70	1.60			
J	0.00	0.10	0.05			
K	0.60	0.80	0.75			
L	0.10	0.30	0.22			
M	0.10	0.20	0.12			
N	0.45	0.65	0.50			
α	0°	8°				
All	All Dimensions in mm					

Suggested Pad Layout



Dimensions	Value (in mm)
Z	1.8
Х	0.4
Y	0.51
С	1.3
Е	0.7



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